



SDI Review Form 1.6

Journal Name:	British Journal of Applied Science & Technology
Manuscript Number:	2014_BJAST_10586
Title of the Manuscript:	CARBON NANO TUBE FIELD EFFECT TRANSISTOR BASED 4-BIT FULL ADDER CELL
Type of the Article	Original Research Article

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

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PART 1: Review Comments

	Reviewer's comment	Author's comment <i>(if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)</i>
<u>Compulsory</u> REVISION comments		
<u>Minor</u> REVISION comments	Author make an interesting design of Ripple carry ahead methodology for an 4-bit full adder using 48 transistors based on CNTFET without any capacitors, although the fabrication will be more complicated by the practical application. Author compared with the CMOS, CNTFET-based adder have some advantages such as more than 44% in power savings and faster 10% via the simulation from H-Spice. Furthermore, author also compared the design with other CNTFET-based adders. However, other 4-bit CNTFET also should be added and compared in the manuscript before published. It also should be note that the graph of Fig. 6 are not clear that should be modified.	I also wanted to compare this design with other 4-bit CNFET based designs but I didn't find any such module. So, I compared the 1-bit design of CNFET with other existing CNFET based designs. I would surely try to clear the graphs of fig. 6.
<u>Optional/General</u> comments		